

EAST - [10812995.wsp 1]

File View Edit Tools Window Help

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DBs: USPAT, US-PGPUB, EPO, JPO ☐ Plurals

Default operator: OR ☒ Highlight all hit terms initially

3 and ((insulat\$3 and substrate and silicon and metallic and metal adj nitride and (metal adj silicide)))

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	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20040056285 A1	20040325	11	Metal spacer gate for CMOS FET	257/288	
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20040036051 A1	20040226	78	Integrated capacitor with enhanced capacitance density and method of	251/301	
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20030197232 A1	20031023	13	Semiconductor device and method of producing the same	257/412	
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20030129831 A1	20030710	16	Asymmetric, double-sided self-aligned silicide and method of forming the same	438/655	257/E23.019
5	<input type="checkbox"/>	<input type="checkbox"/>	US 20030127703 A1	20030710	30	Semiconductor device and method of manufacturing the same	257/520	257/E21.664; 257/E27.104
6	<input type="checkbox"/>	<input type="checkbox"/>	US 20030127640 A1	20030710	13	Semiconductor device and method for manufacturing semiconductor device	257/4	257/E21.274; 257/E29.162;
7	<input type="checkbox"/>	<input type="checkbox"/>	US 20030075744 A1	20030424	25	SEMICONDUCTOR DEVICE ACHIEVING REDUCED WIRING LENGTH AND	257/288	
8	<input type="checkbox"/>	<input type="checkbox"/>	US 20030027393 A1	20030206	16	Semiconductor device and method of manufacturing the same	438/287	257/E21.193; 257/E21.197;
9	<input type="checkbox"/>	<input type="checkbox"/>	US 20020086486 A1	20020704	30	Method of manufacturing semiconductor device and the semiconductor device	438/300	257/382; 257/383;
10	<input type="checkbox"/>	<input type="checkbox"/>	US 20020033520 A1	20020321	49	Semiconductor device	257/577	
11	<input type="checkbox"/>	<input type="checkbox"/>	US 20010030342 A1	20011018	13	Semiconductor device and process for producing the same	257/315	257/E21.199; 257/E21.548;